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| Objective |
| Batch name:  |
| This process flows is a guideline on how to spin, develop and rinse AZ4562 on substrates as Si, SiO2 and SOI, using the SSE Spin coater.  |

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| Step Heading | Equipment |  | Comments |
| 1. Pretreatment
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| * 1. Surface treatment
 | BHF dip *or*250C oven | BHF dip for Si substrates (30 sec, H2O 5 min) Overnight bake  | HMDS pretreatment can course bobbles in resist during exposure.  |
| 1. Spin coat of AZ4562, 10µm
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| * 1. Clean spinner
 | SSE spinner | Clean spinner nozzle and run the dummy wafersRecipe: AZ4562\_10um | 1-3 dummies |
| * 1. Coat wafers
 | SSE Spinner | **Resist:** AZ4562**Recipe:** AZ4562\_10um**Softbake:** is included in the spinning recipe300sec@100C | Resist thickness can be measured with FilmTek recipe: resist\_QC\_9points |
| In case you will have a thicker resist |  | With AZ4562 you can build up the thickness spinning more than one time. Use a lower temperature for softbake between the spinning**Recipe:**….. |  |
| * 1. Coat wafers
 | SSE Spinner | **Repeat step 2.2**  |  |
| 1. Exposure
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| * 1. Exposure
 | Aligner-6inchKS Alignment | **Recipe:** DCH\_10um\_FPA in case you will not alignOr DCH\_10um\_TSA in case you do a Top Side Alignment**Exposure mode:** Hard Contact**Exposure time:** 20sec, to avoid resist overheating use interval exposure**Mask**: your mask**Exposure mode:** Hard Contact**Exposure time:** 40 sec, to avoid resist overheating use multiple exposure**Mask**: your mask | We suggest you do a dose test exposure to find an optimum exposure for your process.Activate interval exposure with 10sec wait time between exposureActivate multiple exposure with 10sec wait time between exposure |
| 1. Development & Rinse
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| * 1. Develop
 | Developer bench | Develop in 351B for 300±10 sec |  |
|  | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).Spin dry |  |
| 1. Inspection
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| * 1. Inspection
 | Optical microscope | Check pattern and alignment marks |  |